

## TRANSIENT VOLTAGE SUPPRESSORS FOR ESD PROTECTION

#### **General Description**

The SESDFBPxxC series are designed to replace multilayer varistors (MLVs) in portable applications such as cell phones,notebook computers,and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs.

#### **Applications**

- Cellular phones handsets and Accessories
- PDA's
- MP3 players
- Digital cameras
- Portable applications
- Mobile telephone

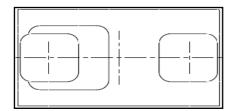
#### **Features**

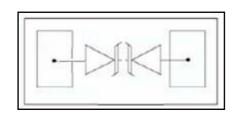
- Equivalent to 0402 package
- 120W peak pulse power
- Small package for use in portable electionics
- Low Leakage current
- These are Pb-Free Devices

# Complies with the following standards IEC61000-4-2

Level 4 15 kV (air discharge) 8 kV(contact discharge) MIL STD 883E - Method 3015-7 Class 3 25 kV HBM (Human Body Model)

### **Functional diagram**





#### WBFBP-02C

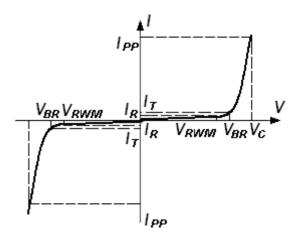
#### Absolute Ratings (T<sub>amb</sub>=25°C) **Symbol Parameter** Value **Units** IEC 61000-4-2 (ESD) Contact 8 kV Peak Pulse Power ( $t_p = 8/20 \mu s$ ) W $P_{PP}$ 120 Peak Pulse Power (t<sub>p</sub> = 8/20μs) 12 $I_{PP}$ Α $T_{\mathsf{L}}$ Maximum lead temperature for soldering during 10s 260 °C Storage Temperature Range -55 to +155 °C Tstg °C $T_i$ Maximum junction temperature -55 to +155



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#### **Electrical Parameter**

Symbol	Parameter						
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current						
Vc	Clamping Voltage @ IPP						
$V_{RWM}$	Working Peak Reverse Voltage						
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>						
Ι <sub>Τ</sub>	Test Current						
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>						

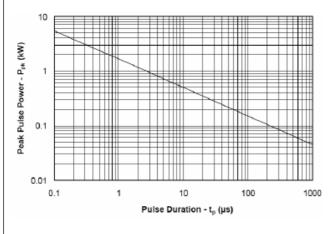


## Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.VF = 0.9V at IF = 10mA

	V <sub>BR</sub>						<b>V</b> F	<b>I</b> F	С
Part Numbers	Min.	Тур.	Max.	lτ	V <sub>RWM</sub>	IR	Max.	Тур.	Typ. 0v bias
	V	V	V	mA	V	μA	V	mA	pF
SESDFBP3V3C	5.1	6.0	6.8	1	3.3	1	-	-	20
SESDFBP05C	6.1	6.6	7.2	1	5.0	1	-	-	15

<sup>\*</sup>Surge current waveform per Figure 1.

## **Typical Characteristics**



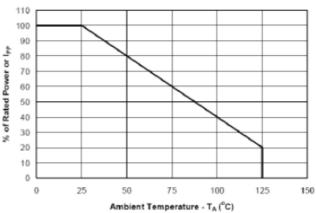


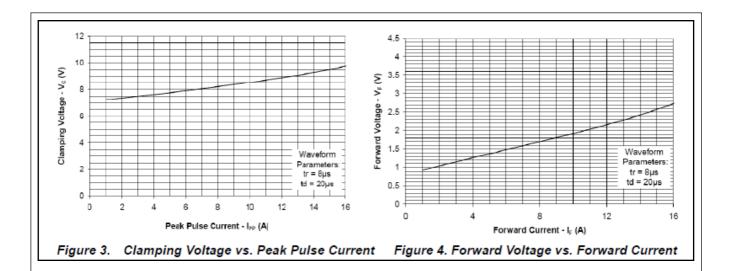
Figure 1. Non-Repetitive Peak Pulse Power versus Pulse Time

Fig 2. Power Derating Curve

<sup>1.</sup>  $V_{BR}$  is measured with a pulse test current  $I_T$  at an ambient temperature of 25  $^{\circ}$ C.



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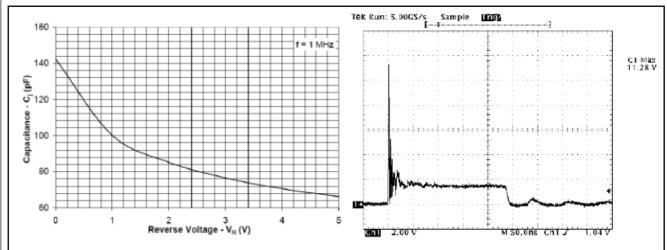
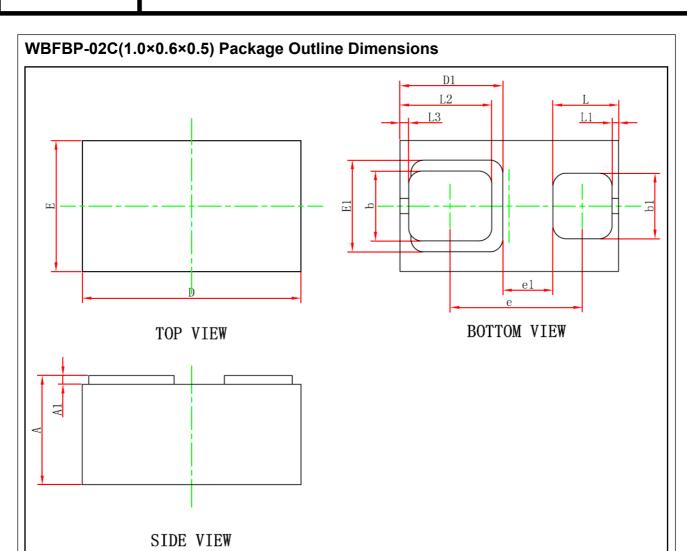


Figure 5.Junction Capacitance vs. Reverse Voltage Fig 6. ESD Clamping (8kV Contact per IEC 61000-4-2)



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Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	0.450	0. 550	0. 018	0.022		
A1	0.010	0. 100	0.000	0.004		
D	0.950	1. 050	0. 037	0.041		
Е	0.550	0.650	0.022	0. 026		
D1	0. 47	OREF.	0.019REF.			
E1	0. 42	OREF.	0.017REF.			
b	0.270	0. 370	0.011	0.015		
b1	0. 250	0. 350	0.010	0.014		
е	0. 555	0. 655	0. 022	0.026		
e1	0. 23	BOREF.	0. 009REF.			
L	0. 250	0.350	0.010	0.014		
L1	0. 03	OREF.	0. 001REF.			
L2	0.370	0. 470	0.015	0.019		
L3	0.04	OREF.	0. 002REF.			